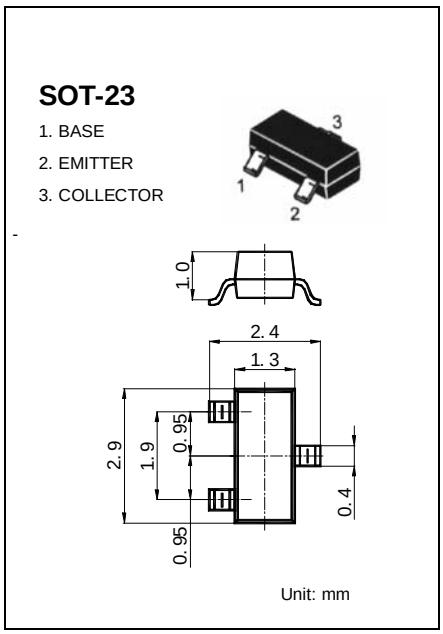
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

MMBT5401LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.3 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -160 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -100 μA, I_E=0	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -1 mA, I_B=0	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-120V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0		-0.1	μA
DC current gain	$H_{FE(1)}$	V_{CE}= -5V, I_C= -1mA	80		
	$H_{FE(2)}$	V_{CE}= -5V, I_C=-10mA	100	200	
	$H_{FE(3)}$	V_{CE}= -5V, I_C=-50mA	50		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-50mA, I_B= -5mA		-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C= -50mA, I_B= -5mA		-1	V
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA f=30MHz	100		MHz

DEVICE MARKING

MMBT5401LT1=2L